Unit in mm

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA1926

POWER AMPLIFIER APPLICATIONS

POWER SWITCHING APPLICATIONS

• Low Collector Saturation Voltage

: $V_{CE (sat)} = -0.17V (Max.) (I_C = -1A)$

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	-80	V
Collector-Emitter Voltage	v_{CEO}	-80	V
Emitter-Base Voltage	$V_{ m EBO}$	-8	V
Collector Current	$I_{\mathbf{C}}$	-3	A
Base Current	$I_{\mathbf{B}}$	-1	A
Collector Power Dissipation	$P_{\mathbf{C}}$	1000	mW
Junction Temperature	$T_{ m j}$	150	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~150	°C

7.1MAX
3.8
3.2
0.55-0.05
0.85
0.45-0.05
0.45-0.05
1. BASE
2. COLLECTOR
3. EMITTER

JEDEC

JEITA

7.1MAX
2.7MAX
1.0
0.65
+0.15
0.45-0.05
1.025±0.05

1.DASE
2.TOLLECTOR
3. EMITTER

2-7D101A

Weight: 0.2g (Typ.)

TOSHIBA

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{ m CBO}$	$V_{CB} = -80V, I_E = 0$	_	_	-1.0	μ A
Emitter Cut-off Current	${ m I}_{ m EBO}$	$V_{EB} = -8V, I_{C} = 0$	_	_	-1.0	μ A
Collector-Emitter Breakdown Voltage	V (BR) CEO	$I_{C} = -10 \text{mA}, I_{B} = 0$	-80	_	_	V
DC Current Gain	h _{FE (1)}	$V_{CE} = -2V, I_{C} = -0.5A$	150	_	400	
	h _{FE (2)}	$V_{CE} = -2V, I_{C} = -1.5A$	40	_	_	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	$I_{C} = -1A, I_{B} = -0.05A$	_	_	-0.17	V
Base-Emitter Saturation Voltage	V _{BE} (sat)	$I_C = -1A, I_B = -0.05A$	_	_	-1.2	V
Transition Frequency	$ m f_{T}$	$V_{CE} = -2V, I_{C} = -0.5A$	_	80	_	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	_	45	_	pF

1 2001-10-29

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